

# **UTC** UNISONIC TECHNOLOGIES CO., LTD

# **UK3019**

# 2.5V DRIVE SILICON N-CHANNEL MOSFET

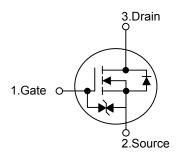
### DESCRIPTION

The UTC UK3019 is a silicon N-channel MOSFET which has been designed to minimize on-state resistance while it provides rugged, reliable and fast switching performance. The product is particularly suited for low voltage, low current applications such as small servo motor controller, power MOSFET gate drivers, and other switching applications.

### **FEATURES**

- \* Min V<sub>DSS</sub> =30V
- \*  $R_{DS(ON)} \le 8.0\Omega$  @  $I_D=10mA$ ,  $V_{GS}=4.0V$
- \*  $R_{DS(ON)} \le 13\Omega$  @  $I_D=1mA$ ,  $V_{GS}=2.5V$
- \* Pulsed ID=400mA
- \* Low Voltage Drive (2.5V)

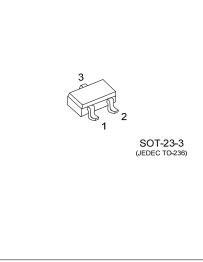
### SYMBOL







**Power MOSFET** 



# ■ ABSOLUTE MAXIMUM RATING (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V <sub>DSS</sub>	30	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V	
Drain Current	Continuous	I <sub>D</sub>	100	mA	
	Pulsed (Note 2)	I <sub>DP</sub>	400	mA	
Power Dissipation (Note 3)		PD	200	mW	
Junction Temperature		TJ	+150	°C	
Storage Temperature		T <sub>STG</sub>	-55 ~ +150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2.  $Pw \le 10\mu s$ , Duty cycle  $\le 50\%$ 

3. With each pin mounted on the recommended lands.

# THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	625	°C/W

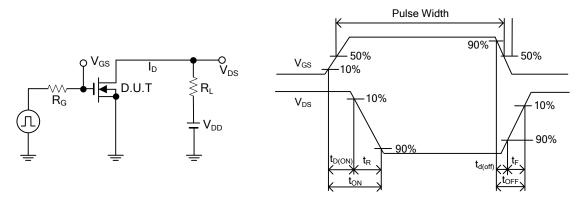
# ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =10µA	30			V
Drain-Source Leakage Current	I <sub>DSS</sub>	$V_{DS}$ =30V, $V_{GS}$ =0V			1	μA
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}=0V, V_{GS}=\pm 20V$			±1	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =3V,I <sub>D</sub> =100µA	0.8		1.5	V
Static drain-source on-state resistance		I <sub>D</sub> =10mA, V <sub>GS</sub> =4.0V		5.0	8.0	Ω
	R <sub>DS(ON)</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =2.5V		7.0	13	Ω
DYNAMIC PARAMETERS						
Input Capacitance	CISS			13		pF
Output Capacitance	C <sub>OSS</sub>	$V_{DS}$ =5V, $V_{GS}$ =0V, f = 1MHz		9		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			4		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	t <sub>D(ON)</sub>			15		ns
Turn-ON Rise Time	t <sub>R</sub>	V <sub>GS</sub> =5V, V <sub>DD</sub> ≈5V		35		ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>	$I_D$ =10mA, R <sub>L</sub> =500Ω, R <sub>G</sub> =10Ω		80		ns
Turn-OFF Fall-Time	t <sub>F</sub>			80		ns



# UK3019

# TEST CIRCUITS AND WAVEFORMS



Switching Time Measurement Circuit

Switching Time Waveforms

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